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AMENDMENTS TO THE CLAIMS

1. (currently amended) A near-hermetic microwave semiconductor device comprising:
a substrate;
a Monolithic Microwave Integrated Circuit (MMIC) disposed on said substrate;
a sealant disposed on said MMIC; and
a Backside Interconnect which connects said substrate to said sealant-coated MMIC, includes plated-through vias disposed on said MMIC, and ties to terminal pins on said substrate.

2. (original) The microwave semiconductor device according to claim 1, wherein said substrate is a PWB suitable for ultrahigh frequency applications.

3. (original) The microwave semiconductor device according to claim 2, wherein said ultrahigh frequency applications include Phased Array Antenna (PAA) systems.

4. (original) The microwave semiconductor device according to claim 2, wherein said substrate is formed of one of a liquid crystal polymer (LCP) and a ceramic.

5. (original) The microwave semiconductor device according to claim 1, wherein said sealant ~~is made of~~ comprises a layer of silicon carbide having a thickness of about 4000 Angstroms.

6. (currently amended) ~~The~~ A near-hermetic microwave semiconductor device ~~according to claim 5 comprising:~~
a substrate;
a Monolithic Microwave Integrated Circuit (MMIC) disposed on said substrate;
a sealant disposed on said MMIC; and
a Backside Interconnect connecting said substrate to said sealant-coated MMIC,

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wherein said ~~silicon carbide~~ sealant is disposed over benzocyclobutene (BCB) as an interlayer dielectric.

7. (original) The microwave semiconductor device according to claim 1, wherein said MMIC is a GaAs MMIC.

8. (currently amended) The microwave semiconductor device according to claim ~~[[5]]~~ 1, wherein ~~said silicon carbide forms a layer of approximately 4000 Angstroms in thickness~~ the device is substantially free of bond wires and solder balls.

9. (currently amended) The microwave semiconductor device according to claim 1, ~~wherein the Backside Interconnect includes plated through ground vias disposed on said MMIC, and which tie to terminal pins on said substrate~~ further comprising a plurality of rest vias connecting the MMIC to a bottom ground plane of the substrate.

10. (currently amended) The microwave semiconductor device according to claim 1, further comprising a solder attachment along a periphery of said MMIC, to near-hermetically seal said MMIC to said substrate.

11. (original) The microwave semiconductor device according to claim 10, wherein the said solder attachment is formed using AuSn solder.

12. (original) The microwave semiconductor device according to claim 1, further comprising a conformal coating disposed on said sealant.

13. (currently amended) The microwave semiconductor device according to claim 12, further comprising a cover disposed ~~on~~ over said conformal-coated MMIC in a non-contacting manner.

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14. (original) The microwave semiconductor device according to claim 1, further comprising a cover disposed on said MMIC.

15. (currently amended) A near-hermetic device comprising:
a substrate;
an electronics package disposed on said substrate;
a sealant disposed on said electronics package; and
a Backside Interconnect which connects said substrate to said sealant-coated electronics package; and
an interlayer dielectric disposed between said sealant and said electronics package.

16. (original) The near-hermetic device according to claim 15, wherein said electronics package is solder-attached to seal said electronics package to said substrate.

17. (currently amended) A near-hermetic microwave semiconductor device, comprising:
a substrate;
a Monolithic Microwave Integrated Circuit (MMIC) disposed on said substrate;
a sealant disposed on said MMIC;
a Backside Interconnect which connects said substrate to said sealant-coated MMIC; and
a conformal coating disposed on said sealant; and
a cover disposed on said device without directly contacting said coating.

18. (currently amended) ~~[[A]]~~ The near-hermetic microwave semiconductor device according to claim 17, comprising:
~~a substrate;~~
~~a Monolithic Microwave Integrated Circuit (MMIC) disposed on said substrate;~~

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~~a sealant disposed on said MMIC;~~
~~a Backside Interconnect which connects said substrate to said sealant coated~~
~~MMIC; and~~
~~a protective cover disposed on said sealant coated MMIC~~
wherein the device is substantially free of solder balls and bond pads and said
coating is a low dielectric having a dielectric constant of between about 2 GHz and
about 10 GHz.

19-26. (canceled)

27. (new) The microwave semiconductor device according to claim 6, wherein said substrate is a PWB suitable for ultrahigh frequency applications.

28. (new) The microwave semiconductor device according to claim 27, wherein said ultrahigh frequency applications include Phased Array Antenna (PAA) systems.

29. (new) The microwave semiconductor device according to claim 27, wherein said substrate is formed of one of a liquid crystal polymer (LCP) and a ceramic.

30. (new) The microwave semiconductor device according to claim 6, wherein said sealant comprises a layer of silicon carbide.

31. (new) The microwave semiconductor device according to claim 6, wherein said MMIC is a GaAs MMIC.

32. (new) The microwave semiconductor device according to claim 6, further comprising a solder attachment along a periphery of said MMIC, to seal said MMIC to said substrate.

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33. (new) The microwave semiconductor device according to claim 6, further comprising a conformal coating disposed on said sealant.

34. (new) The microwave semiconductor device according to claim 6, further comprising a cover disposed on said MMIC.